

Fast switching diode

Features:

- 1700V technology, Emitter Controlled Diode 3th generation, 200 µm chip
- soft, fast switching
- low reverse recovery charge
- small temperature coefficient

This chip is used for:

power modules



Applications:

· resonant applications, drives

Chip Type	V_{R}	I _F	Die Size	Package
SIDC112D170H	1700V	205A	11.8 x 9.52 mm ²	sawn on foil

Mechanical Parameters

Mechanica i dianicters			
Raster size	11.8 x 9.52		
Area total	112.3	mm²	
Anode pad size	9.78 x 7.5		
Thickness	200	μm	
Wafer size	150	mm	
Max. possible chips per wafer	114		
Passivation frontside	Photoimide		
Pad metal	3200 nm AlSiCu		
Backside metal	Ni Ag –system suitable for epoxy and soft solder die bonding		
Die bond	Electrically conductive glue or solder		
Wire bond	AI, ≤500μm		
Reject ink dot size	Ø 0.65mm; max 1.2mm		
Recommended storage environment	Store in original container, in dry nitrogen, in dark environment, < 6 month at an ambient temperature of 23°C		



Maximum Ratings

Parameter	Symbol	Condition	Value	Unit	
Repetitive peak reverse voltage	V_{RRM}	T _{vj} = 25 °C	1700	V	
Continuous forward current	I _F	<i>T</i> _{vj} < 150°C	1)	Α	
Maximum repetitive forward current	I _{FRM}	<i>T</i> _{vj} < 150°C	410] ^	
Junction temperature range	T_{vj}		-40+175	°C	
Operating junction temperature	T_{vj}		-40+150	°C	
Dynamic ruggedness ²⁾	P _{max}	$I_{\text{Fmax}} = 410\text{A}, \ V_{\text{Rmax}} = 1700\text{V}, \ T_{\text{vj}} \le 150^{\circ}\text{C}$	tbd	kW	

¹⁾ depending on thermal properties of assembly

Static Characteristic (tested on wafer), T_{vj} = 25 °C

Parameter	Symbol	Conditions	Value			Unit
raiaillelei			min.	typ.	max.	Oilit
Reverse leakage current	I_{R}	V _R =1700V			20	μA
Cathode-Anode breakdown Voltage	V_{BR}	I _R =0.25mA	1700			V
Diode forward voltage	V _F ³⁾	/ _F =205A		1.9	2.3	V

³⁾ V_F tested at lower current

Further Electrical Characteristics

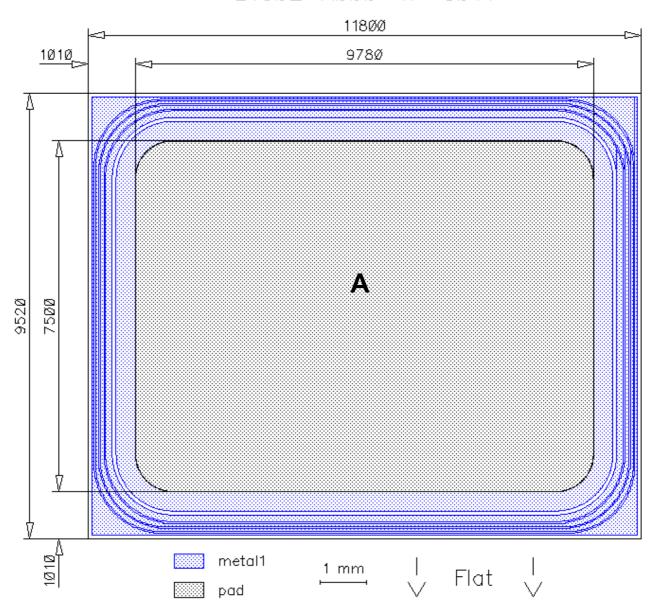
Switching characteristics and thermal properties are depending strongly on module design and mounting technology and can therefore not be specified for a bare die.

²⁾ not subject to production test - verified by design/characterisation



Chip Drawing

Die-Size 11800 um x 9520 um L4502-A000-1P-S011



A: Anode pad



FURTHER EL	ECTRICAL CHARACTERISTICS			
This chip da module data	ita sheet refers to the a sheet			
DESCRIPTION	N			
AQL 0,65 for v	risual inspection according to failu	re catalogue		
Electrostatic D	ischarge Sensitive Device accord	ing to MIL-STD 883		
REVISION HIS	STORY			
Version	Subjects (major o	changes since last revision	on)	Date

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